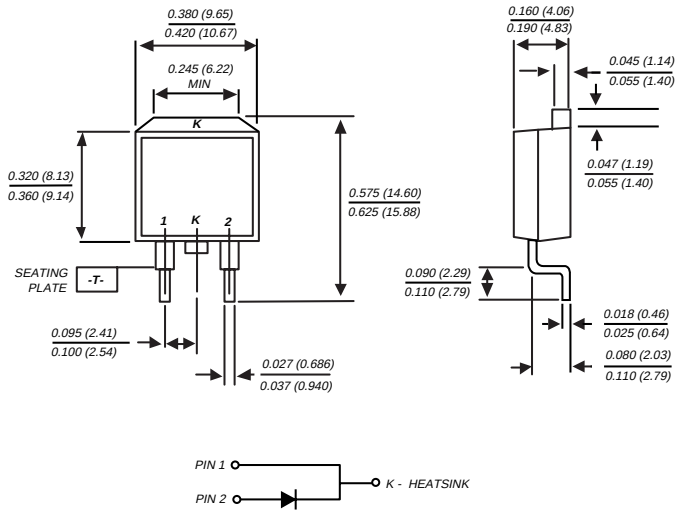
查询BYWB29-100供应商

BYWB29-50 THRU BYWB29-200

FAST EFFICIENT PLASTIC RECTIFIER

***Reverse Voltage** - 50 to 200 Volts* ***Forward Current** - 8.0 Amperes*

TO-263



Dimensions in inches and (millimeters)

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junction
- Low power loss
- Low leakage current
- High surge current capability
- Superfast recovery time for high efficiency
- High temperature soldering in accordance with CECC 802 / Reflow guaranteed

MECHANICAL DATA

Case: JEDEC TO-263AB molded plastic body
Terminals: Plated lead solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any
Weight: 0.08 ounce, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	BYWB29-50	BYWB29-100	BYWB29-150	BYWB29-200	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	Volts
Maximum RMS voltage	V_{RMS}	35	70	105	140	Volts
Maximum DC blocking voltage	V_{DC}	50	100	150	200	Volts
Maximum average forward rectified current at T_C=125°C	$I_{(AV)}$	8.0				Amps
Peak forward surge current 10ms single half sine-wave superimposed T_J=150°C	I_{FSM}	100.0				Amps
Maximum instantaneous forward voltage at: I_F=20A, T_J=25°C I_F=8A, T_J=150°C	V_F	1.3 0.8				Volts
Maximum DC reverse current at rated DC blocking voltage T_C=25°C T_C=100°C	I_R	10.0 500.0				µA
Maximum reverse recovery time (NOTE 1)	t_{rr}	25.0				ns
Typical junction capacitance (NOTE 2)	C_J	45.0				pF
Maximum thermal resistance (NOTE 3)	$R_{\Theta JC}$	3.0				°C/W
Operating and storage temperature range	T_J, T_{STG}	-65 to +150				°C

NOTES:
(1) Reverse recovery test conditions: I_F=1A, V_R=30V, di/dt=100A/µs, I_{rr}=10%, I_{RM} for measurement of t_{rr}
(2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
(3) Thermal resistance from junction to case mounted on heatsink

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RATINGS AND CHARACTERISTIC CURVES BYWB29-50 THRU BYWB29-200

FIG. 1 - MAXIMUM FORWARD CURRENT DERATING CURVE

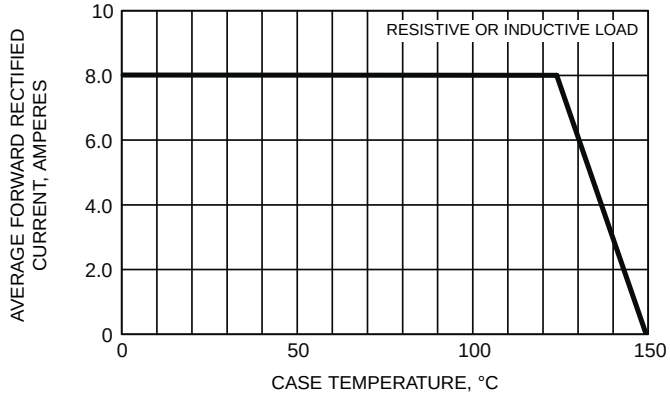


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

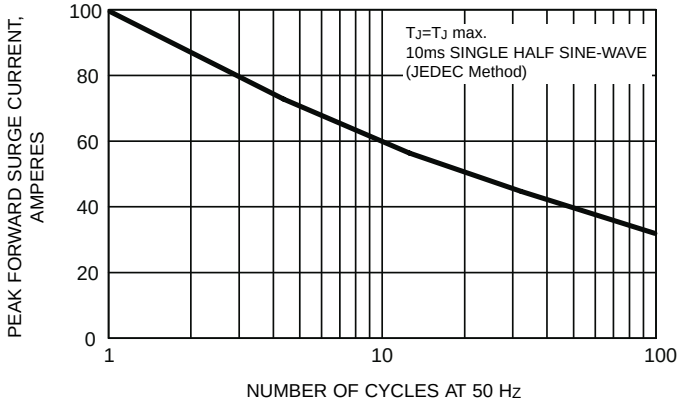


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

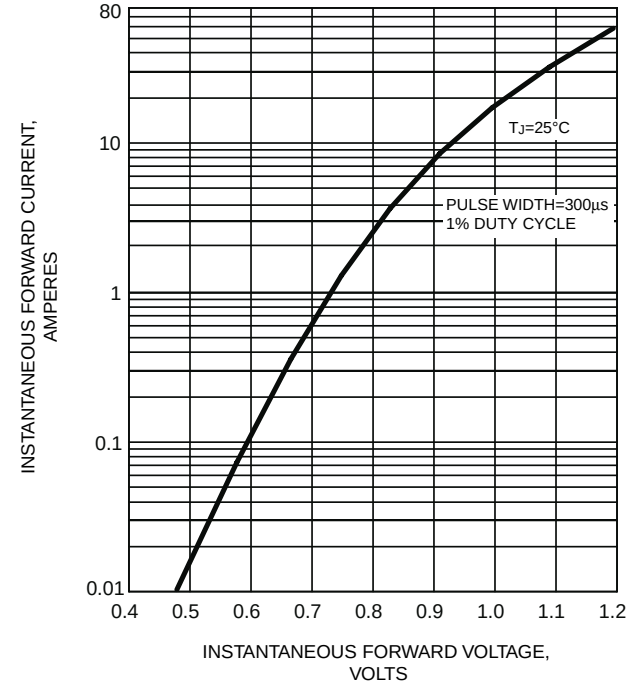


FIG. 4 - TYPICAL REVERSE LEAKAGE CHARACTERISTICS

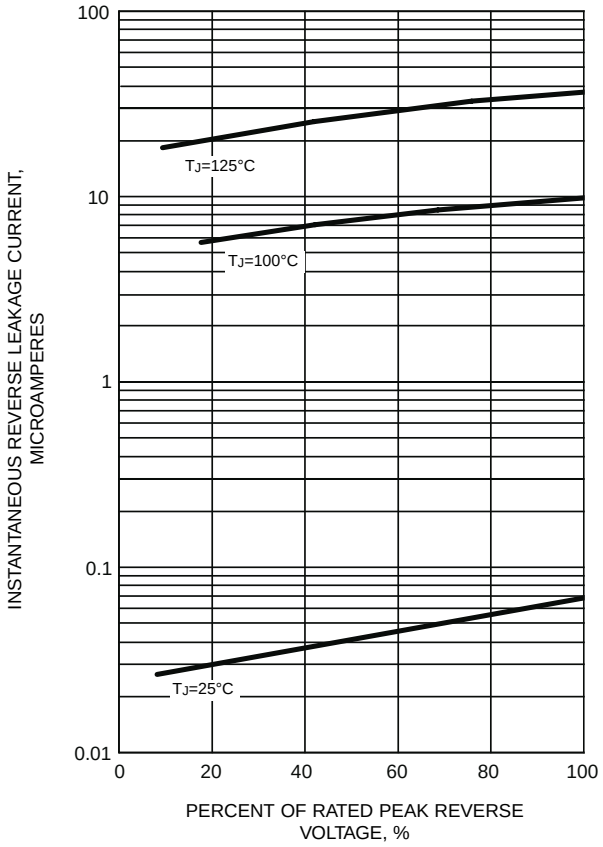
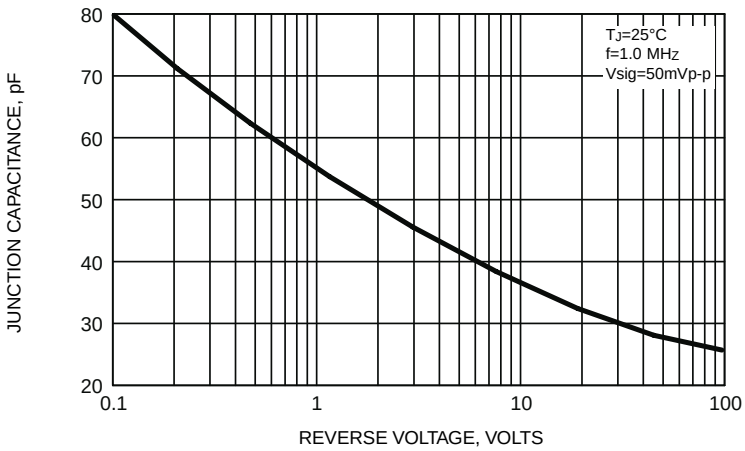


FIG. 5 - TYPICAL JUNCTION CAPACITANCE



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